



- 1. High reliability
- 2. Low reverse current and low forward voltage



Low current rectification and high speed switching

Silicon epitaxial planar

$T_j=25^{\circ}\text{C}$

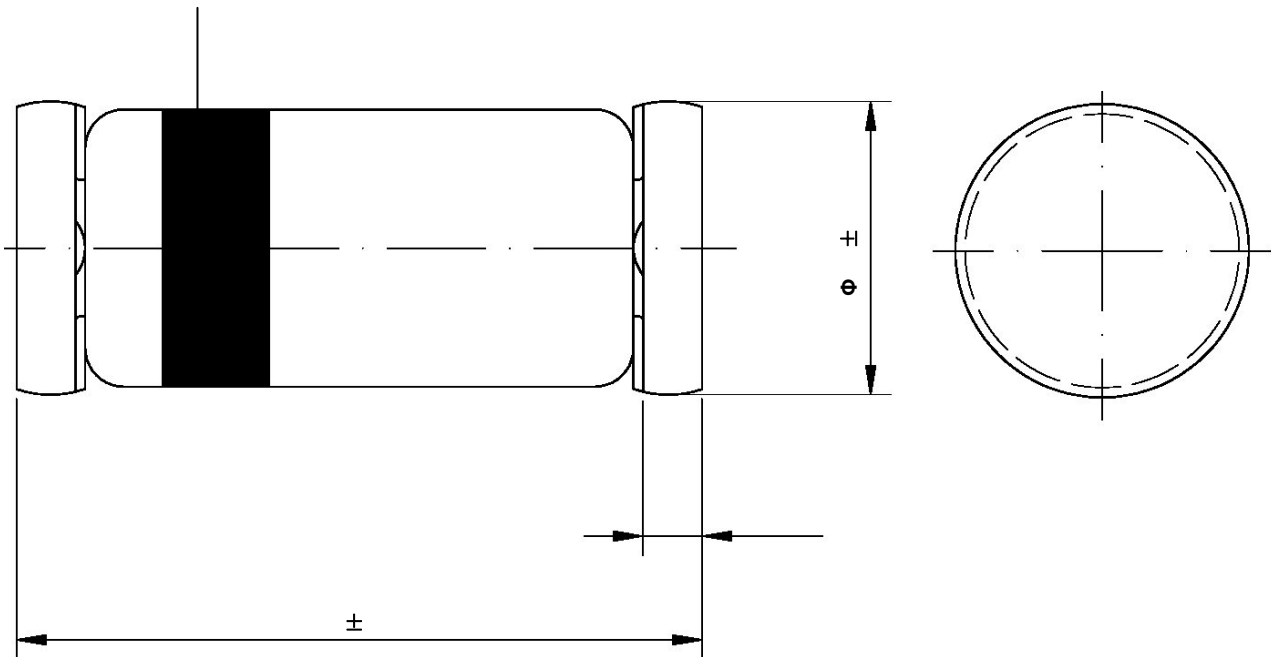
Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		LL60	V_{RRM}	40	V
		LL60P	V_{RRM}	45	V
Peak forward surge current	$t_p \leq 1 \text{ s}$	LL60	I_{FSM}	150	mA
		LL60P	I_{FSM}	500	mA
Forward continuous current	$T_a=25^{\circ}\text{C}$	LL60	I_F	30	mA
		LL60P	I_F	50	mA
Storage temperature range			T_{stg}	-65~+125	$^{\circ}\text{C}$

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.



T_j=25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =1mA	LL60	V _F		0.32	0.5	V
		LL60P	V _F		0.24	0.5	V
	I _F =30mA	LL60	V _F		0.65	1.0	V
	I _F =200mA	LL60P	V _F		0.65	1.0	V
Reverse current	V _R =15V	LL60	I _R		0.1	0.5	μA
		LL60P	I _R		0.5	1.0	μA
Junction capacitance	V _R =1V, f=1MHz	LL60	C _J		2.0		pF
	V _R =10V, f=1MHz	LL60P	C _J		6.0		pF
Reverse recovery time	I _F =I _R =1mA I _{tr} =1mA R _C =100		t _{rr}			1.0	ns



Glass Case
 Mini Melf / SOD-80
 JEDEC DO-213 AA

Excel Semiconductor